

AMENDMENTS TO THE SPECIFICATION

- Please amend the Title which begins on page 1, line 1, as follows:

~~THYRISTOR-BASED SRAM AND METHOD USING QUASI-PLANAR
DOUBLE GATED FIN FIELD EFFECT TRANSISTOR FINFET PROCESS
FOR THE FABRICATION THEREOF OF A THYRISTOR-BASED
STATIC READ/WRITE RANDOM-ACCESS MEMORY~~